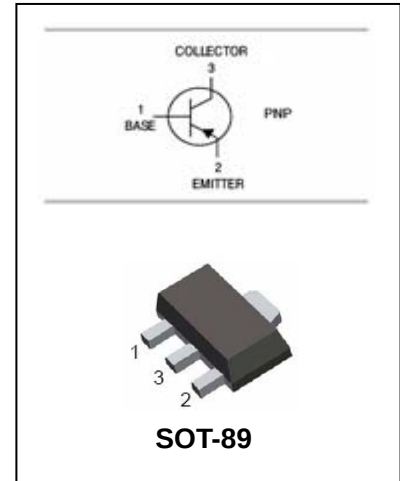


Plastic-Encapsulated Transistor**2SA1664****FEATURES**

- Complementary to 2SC2884

**ORDERING INFORMATION**

Type No.	Marking	Package Code
2SA1664	RO/RV	SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-0.8	A
P _C	Collector Power Dissipation	500	mW
T _j , T _{stg}	Junction and Storage Temperature	-55~150	℃

Plastic-Encapsulated Transistor**2SA1664****ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35			V
Collector- emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter- base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	100		320	
		$V_{CE}=-1V, I_C=-700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$			-0.7	V
Base-emitter	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5		-0.8	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		19		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	RO	RY

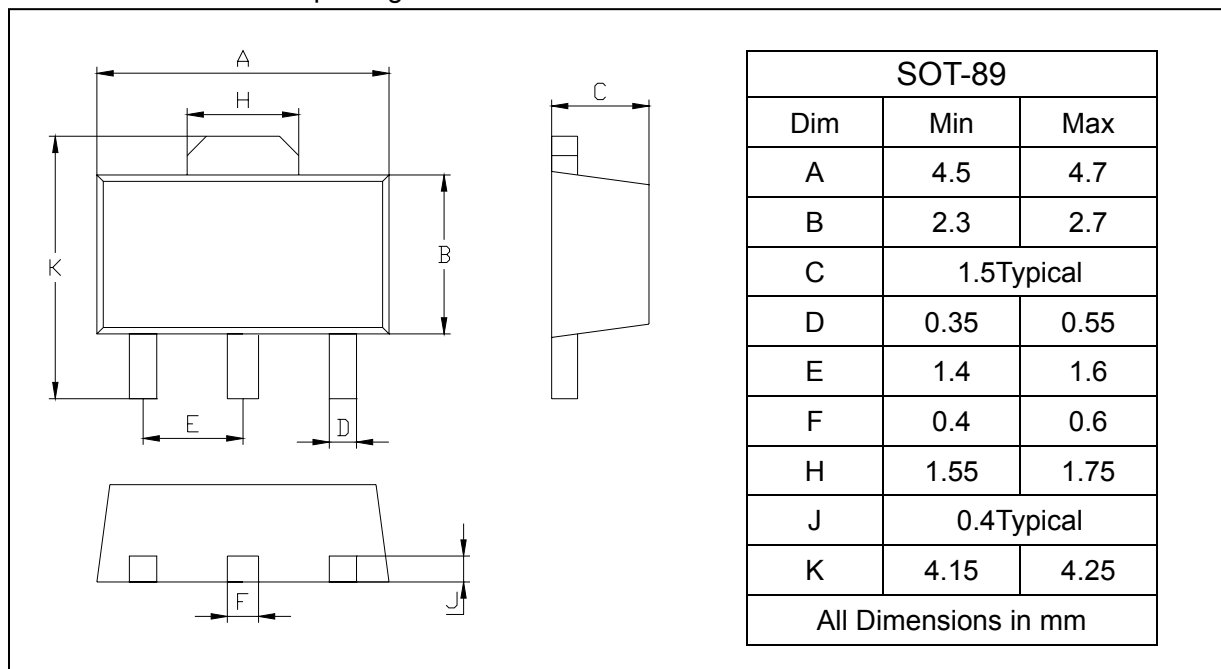
Plastic-Encapsulated Transistor

2SA1664

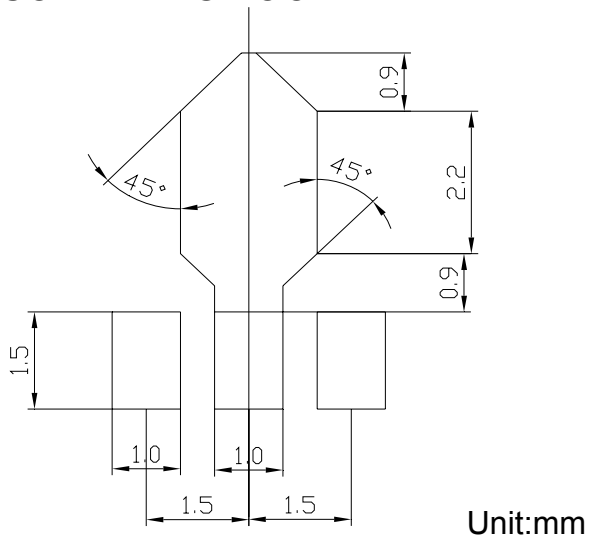
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1664	SOT-89	1000/Tape&Reel